

NTE106 Silicon PNP Transistor Switching Transistor

Electrical Characteristics: (T_A = +25°C unless otherwise specified)

| Parameter | Symbol | Test Conditions | Min | Тур | Max | Unit | | | | | |
|-------------------------------------|----------------------|--|-----|-----|-----|------|--|--|--|--|--|
| OFF Characteristics | | | | | | | | | | | |
| Collector–Emitter Breakdown Voltage | V _{(BR)CEO} | $I_C = 3mA$, $I_B = 0$, Note 1 | 15 | _ | _ | V | | | | | |
| | V _{(BR)CES} | $I_C = 100 \mu A, V_{BE} = 0$ | 15 | _ | _ | V | | | | | |
| Collector-Base Breakdown Voltage | V _{(BR)CBO} | $I_C = 100 \mu A, I_E = 0$ | 15 | _ | _ | V | | | | | |
| Emitter-Base Breakdown Voltage | V _{(BR)EBO} | $I_E = 100 \mu A, I_C = 0$ | 4.5 | 5.9 | _ | V | | | | | |
| Collector Cutoff Current | I _{CES} | $V_{CE} = 8V, V_{BE} = 0$ | _ | _ | 10 | nA | | | | | |
| | | $V_{CE} = 8V, V_{BE} = 0, T_A = +125^{\circ}C$ | _ | _ | 5 | μΑ | | | | | |
| Base Current | Ι _Β | $V_{CE} = 8V, V_{BE} = 0$ | _ | _ | 1 | nA | | | | | |
| ON Characteristics | | | | | | | | | | | |
| DC Current Gain | h _{FE} | $I_C = 1 \text{mA}, V_{CE} = 500 \text{mV}$ | 35 | _ | _ | | | | | | |
| | | I _C = 10mA, V _{CE} = 300mV | 50 | _ | 120 | | | | | | |
| | | $I_C = 10 \text{mA}, V_{CE} = 300 \text{mV}, T_A = -55 ^{\circ}\text{C}$ | 20 | _ | _ | | | | | | |
| | | I _C = 50mA, V _{CE} = 1V, Note 1 | 40 | _ | _ | | | | | | |

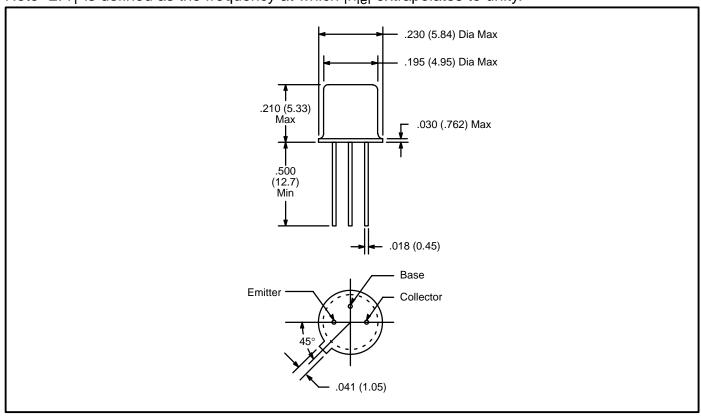
Note 1. Pulse Test: Pulse Width $\leq 300 \mu s$, Duty Cycle $\leq 2\%$.

<u>Electrical Characteristics (Cont'd)</u>: $(T_A = +25^{\circ}C)$ unless otherwise specified)

| Parameter | Symbol | Test Conditions | Min | Тур | Max | Unit |
|--------------------------------------|----------------------|---|------|------|------|------|
| ON Characteristics (Cont'd) | | | | | | |
| Collector–Emitter Saturation Voltage | V _{CE(sat)} | I _C = 1mA, I _B = 0.1mA | _ | _ | 0.15 | V |
| | | I _C = 10mA, I _B = 1mA | _ | _ | 0.18 | V |
| | | $I_C = 50$ mA, $I_B = 5$ mA, Note 1 | _ | _ | 0.6 | V |
| Base–Emitter Saturation Voltage | V _{BE(sat)} | $I_C = 1mA$, $I_B = 0.1mA$ | _ | 0.7 | 0.8 | V |
| | | I _C = 10mA, I _B = 1mA | 0.75 | 0.86 | 0.90 | V |
| | | $I_C = 50$ mA, $I_B = 5$ mA, Note 1 | _ | 1.1 | 1.5 | V |
| Small-Signal Characteristics | | | | | | |
| Current Gain-Bandwidth Product | f _T | I _C = 10mA, V _{CE} = 10V, f = 100MHz | 850 | 1100 | _ | MHz |
| Output Capacitance | C _{obo} | $V_{CB} = 5V, I_E = 0, f = 140kHz$ | - | 2.0 | 3.0 | pF |
| Input Capacitance | C _{ibo} | $V_{BE} = 500 \text{mV}, I_{C} = 0, f = 140 \text{kHz}$ | _ | 2.0 | 3.5 | pF |
| Switching Characteristics | | | | | | |
| Turn-On Time | t _{on} | $V_{CC} = 1.5V$, $V_{BE} = 0$, $I_{C} = 10$ mA, $I_{B1} = 1$ mA | _ | 10 | 15 | ns |
| Delay Time | t _d | | _ | 5 | 10 | ns |
| Rise Time | t _r | | _ | 5 | 15 | ns |
| Turn-Off Time | t _{off} | $V_{CC} = 1.5V, I_C = 10mA,$ $I_{B1} = I_{B2} = 1mA$ | _ | 16 | 20 | ns |
| Stoirage Time | t _s | | _ | 17 | 20 | ns |
| Fall Time | t _f | | _ | 8 | 10 | ns |
| Storage Time | t _s | I _C = 10mA, I _{B1} = 10mA, I _{B2} = 10mA | _ | _ | 20 | ns |

Note 1. Pulse Test: Pulse Width $\leq 300 \mu s$, Duty Cycle $\leq 2\%$.

Note 2. f_T is defined as the frequency at which $|h_{fe}|$ extrapolates to unity.



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